

DESCRIPTION

ELECTRONIC APPARATUS

5 **Technical Field**

The present invention relates to an electronic apparatus and a thermal conversion apparatus, and, more particularly, to an electronic apparatus and a thermal conversion apparatus, having a thermoelectric conversion element.

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Background Art

A thermoelectric conversion element is used to convert thermal energy into electric energy using Seebeck effect. Japanese Unexamined Patent Publication No. 2000-244023
15 discloses a thermoelectric conversion apparatus using Seebeck effect of a semiconductor.

Disclosure

Technical Problem

20 There is a need for an electronic apparatus wherein a thermoelectric conversion element and at least one of a photoelectric conversion element and a transistor or a diode are integrated. However, because monolithic integration of the thermoelectric conversion element and at least one of the
25 photoelectric conversion element and the transistor or the

diode is difficult, hybrid integration thereof has been carried out to date.

In the case where a thermoelectric conversion apparatus includes a p-type thermoelectric conversion unit including a
5 p-type semiconductor layer responsible for thermoelectric conversion and an n-type thermoelectric conversion unit including an n-type semiconductor layer responsible for thermoelectric conversion, the p-type thermoelectric conversion unit may interfere with the n-type thermoelectric
10 conversion unit.

Accordingly, the present invention has been made keeping in mind the above problems, and an object of the present invention is to provide an electronic apparatus, which enables the monolithic integration of a thermoelectric conversion
15 element and at least one of a photoelectric conversion element and a transistor or a diode or which prevents the interference between a p-type thermoelectric conversion unit and an n-type thermoelectric conversion unit.

20 **Technical Solution**

The present invention provides an electronic apparatus, comprising a thermoelectric conversion element including a semiconductor layer which performs thermoelectric conversion, and at least one of a photoelectric conversion element in
25 which at least a portion of the semiconductor layer performs

photoelectric conversion and a transistor or a diode having at least a portion of the semiconductor layer as an operating layer. According to the present invention, the thermoelectric conversion element and at least one of the photoelectric conversion element and the transistor or the diode may be monolithically integrated.

The present invention provides an electronic apparatus, comprising a thermoelectric conversion element including a semiconductor layer which performs thermoelectric conversion using Seebeck effect, and at least one of a photoelectric conversion element in which at least a portion of the semiconductor layer performs photoelectric conversion and a transistor or a diode having at least a portion of the semiconductor layer as an operating layer, wherein the semiconductor layer has bandgap energy corresponding to UV (UltraViolet) light, the thermoelectric conversion element has an IR (InfraRed) absorption part which absorbs IR rays and converts them into heat, and at least the portion of the semiconductor layer of the photoelectric conversion element performs photoelectric conversion of UV light. According to this construction, the photoelectric conversion element which detects UV light and the thermoelectric conversion element which detects IR rays may be monolithically integrated.

The present invention provides an electronic apparatus, comprising a thermoelectric conversion element including a

semiconductor layer which performs thermoelectric conversion using Seebeck effect, and at least one of a photoelectric conversion element in which at least a portion of the semiconductor layer performs photoelectric conversion and a
5 transistor or a diode having at least a portion of the semiconductor layer as an operating layer, wherein the semiconductor layer has bandgap energy corresponding to IR rays, the thermoelectric conversion element has an IR absorption part which absorbs IR rays and converts them into
10 heat, and at least the portion of the semiconductor layer of the photoelectric conversion element performs photoelectric conversion of IR rays. According to this construction, the thermoelectric conversion element which detects wide-range IR rays and the photoelectric conversion element which detects IR
15 rays corresponding to the bandgap energy of the semiconductor layer may be monolithically integrated.

In the above construction, the semiconductor layer may include a p-type semiconductor layer and an n-type semiconductor layer which are stacked, and the thermoelectric
20 conversion element may include a p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion and an n-type thermoelectric conversion unit wherein the n-type semiconductor layer performs thermoelectric conversion.
25 According to this construction, thermoelectric conversion may

be carried out at high sensitivity.

The present invention provides an electronic apparatus, comprising a thermoelectric conversion element including a semiconductor layer which performs thermoelectric conversion
5 using Seebeck effect, and at least one of a photoelectric conversion element in which at least a portion of the semiconductor layer performs photoelectric conversion and a transistor or a diode having at least a portion of the semiconductor layer as an operating layer, wherein the
10 semiconductor layer includes a p-type semiconductor layer and an n-type semiconductor layer which are stacked, the thermoelectric conversion element includes a p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion and an
15 n-type thermoelectric conversion unit wherein the n-type semiconductor layer performs thermoelectric conversion, and the photoelectric conversion element is a photodiode that uses the p-type semiconductor layer and the n-type semiconductor layer. According to this construction, monolithic integration
20 of the thermoelectric conversion element and the photoelectric conversion element becomes much more feasible.

In the above construction, an isolation part may be provided between the p-type thermoelectric conversion unit and the n-type thermoelectric conversion unit so as to
25 electrically isolate the p-type semiconductor layer and the n-

type semiconductor layer. According to this construction, interference between the p-type semiconductor layer and the n-type semiconductor layer may be prevented.

In the above construction, an ohmic electrode formed on the semiconductor layer disposed at an upper position among the p-type semiconductor layer and the n-type semiconductor layer may be a non-alloy ohmic electrode, and an ohmic electrode formed on the semiconductor layer disposed at a lower position among the p-type semiconductor layer and the n-type semiconductor layer may be an alloy ohmic electrode. According to this construction, the ohmic electrode formed on the semiconductor layer at the upper position may be prevented from being electrically connected to the ohmic electrode formed on the semiconductor layer at the lower position.

In the above construction, the semiconductor layer may have a modulation doped structure. According to this construction, both desired sensitivity and detectability of the thermoelectric conversion element may be obtained.

In the above construction, the thermoelectric conversion element and the photoelectric conversion element may be provided in plural numbers such that the plurality of thermoelectric conversion elements and the plurality of photoelectric conversion elements are arranged in a matrix shape, and a selection part may be provided so as to select at least one among the plurality of thermoelectric conversion

elements and the plurality of photoelectric conversion elements and may include the transistor.

The present invention provides a thermoelectric conversion apparatus, comprising a semiconductor layer including a p-type semiconductor layer and an n-type semiconductor layer which are stacked, a first thermoelectric conversion element including a first n-type thermoelectric conversion unit wherein the n-type semiconductor layer performs thermoelectric conversion and a first p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion, a second thermoelectric conversion element including a second n-type thermoelectric conversion unit wherein the n-type semiconductor layer performs thermoelectric conversion and a second p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion, a first beam including the first n-type thermoelectric conversion unit and the second p-type thermoelectric conversion unit, a second beam including the first p-type thermoelectric conversion unit and the second n-type thermoelectric conversion unit, and a central region to which the first beam and the second beam are connected and which includes a first isolation part for electrically isolating at least one of the p-type semiconductor layer and the n-type semiconductor layer between the first thermoelectric

conversion element and the second thermoelectric conversion element, wherein the first thermoelectric conversion element and the second thermoelectric conversion element are connected in a series so that the first n-type thermoelectric conversion unit and the second p-type thermoelectric conversion unit are connected. According to the present invention, electrical interference between the first thermoelectric conversion element and the second thermoelectric conversion element may be prevented.

10 In the above construction, the first beam may include a second isolation part for electrically isolating the first n-type thermoelectric conversion unit and the second p-type thermoelectric conversion unit, and the second beam may include a third isolation part for electrically isolating the first p-type thermoelectric conversion unit and the second n-type thermoelectric conversion unit. According to this construction, electrical interference between the first thermoelectric conversion element and the second thermoelectric conversion element may be further prevented.

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Advantageous Effects

According to the present invention, a thermoelectric conversion element and at least one of a photoelectric conversion element and a transistor or a diode can be monolithically integrated.

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Description of Drawings

FIG. 1 is a cross-sectional view showing an electronic apparatus according to a first embodiment;

5 FIGS. 2(a) ~ 2(d) are cross-sectional views showing a process of manufacturing a thermoelectric conversion element 100;

FIG. 3 shows the bandgap energy with respect to the lattice constant of a variety of semiconductors;

10 FIG. 4 is a cross-sectional view showing a modification of the first embodiment;

FIG. 5 is a cross-sectional view showing a thermoelectric conversion apparatus according to a second embodiment;

15 FIG. 6 is a top plan view showing the thermoelectric conversion apparatus;

FIGS. 7(a) and 7(b) are top plan views showing modifications of the second embodiment;

FIGS. 8(a) to 8(c) are top plan views showing the other modifications of the second embodiment;

20 FIG. 9(a) shows the sensitivity R of a thermoelectric conversion apparatus using AlGa_N/Ga_N with respect to changes in L and W , and FIG. 9(b) shows the detectability D and the response time τ with respect to changes in L and W ;

FIG. 10(a) shows the sensitivity R of a thermoelectric
25 conversion apparatus using MgZnO/ZnO with respect to changes

in L and W, and FIG. 10(b) shows the detectability D and the response time τ with respect to changes in L and W;

FIG. 11(a) shows the sensitivity R of a thermoelectric conversion apparatus using AlGaAs/InGaAs with respect to
5 changes in L and W, and FIG. 11(b) shows the detectability D and the response time τ with respect to changes in L and W;
and

FIG. 12 is a block diagram showing a fourth embodiment.

<Description of the Reference Numerals in the Drawings>

- 10 10: substrate 12: cavity
- 20: n-type semiconductor layer
- 30: p-type semiconductor layer
- 42: isolation part 48: absorption part
- 60: column selection part 62: row selection part
- 15 64: selective transistor 70a: first beam
- 70b: second beam 72: central region
- 90: n-type thermoelectric conversion unit
- 92: p-type thermoelectric conversion unit
- 100: thermoelectric conversion element
- 20 102: photoelectric conversion element 104: transistor

Best Mode

Hereinafter, embodiments of the present invention are described with reference to the drawings.

25 (First Embodiment)

FIG. 1 is a cross-sectional view showing an electronic apparatus according to a first embodiment. A thermoelectric conversion element 100, a photoelectric conversion element 102 and a transistor 104 are formed on a substrate 10. Sequentially placed on the substrate 10 made of Si are an etching stop layer 14, an n-type semiconductor layer 20, an electrical isolation layer 28 and a p-type semiconductor layer 30. A semiconductor layer 38 includes the n-type semiconductor layer 20, the electrical isolation layer 28 and the p-type semiconductor layer 30. The thermoelectric conversion element 100 includes a p-type thermoelectric conversion unit 92 and an n-type thermoelectric conversion unit 90. The semiconductor layer 38 between the thermoelectric conversion element 100, the photoelectric conversion element 102 and the transistor 104 is isolated by means of an isolation part 42 that is formed up to the upper surface of the etching stop layer 14. The p-type thermoelectric conversion unit 92 and the n-type thermoelectric conversion unit 90 are isolated by means of an isolation part 42 that is formed up to the upper surface of the etching stop layer 14.

In the p-type thermoelectric conversion unit 92, p-type ohmic electrodes 46 are formed at both sides on the p-type semiconductor layer 30. A passivation layer 40 is formed on the p-type semiconductor layer 30 between the p-type ohmic

electrodes 46. In the n-type thermoelectric conversion unit 90, the p-type semiconductor layer 30 and the electrical isolation layer 28 are removed, and n-type ohmic electrodes 44 are formed at both sides on the n-type semiconductor layer 20.

5 A passivation layer 40 is formed on the n-type semiconductor layer 20 between the n-type ohmic electrodes 44. An absorption part 48 is provided on one p-type ohmic electrode 46 and one n-type ohmic electrode 44 at a position where the p-type thermoelectric conversion unit 92 and the n-type

10 thermoelectric conversion unit 90 are in contact. Cold pads 50 are respectively formed on the other p-type ohmic electrode 46 and the other n-type ohmic electrode 44. Furthermore, a cavity 12 is formed on the substrate 10 under the p-type thermoelectric conversion unit 92 and the n-type

15 thermoelectric conversion unit 90.

In the photoelectric conversion element 102, p-type ohmic electrodes 52 are formed on the p-type semiconductor layer 30. A passivation layer 40 is formed on the p-type semiconductor layer 30 on which the p-type ohmic electrodes 52 are not

20 formed. The passivation layer 40 may be formed of a material that permits light to pass therethrough at a wavelength at which the photoelectric conversion element 102 performs photoelectric conversion.

In the transistor 104, the p-type semiconductor layer 30

25 and the electrical isolation layer 28 are removed, and n-type

ohmic electrodes 54 (e.g. a source electrode and a drain electrode) and a gate electrode 56 are provided on the n-type semiconductor layer 20. Furthermore, a passivation layer 40 is formed on the n-type semiconductor layer 20 between the n-type ohmic electrodes 54 and the gate electrode 56.

The layers ranging from the etching stop layer 14 to the p-type semiconductor layer 30 may be formed using for example MOCVD (Metal Organic Chemical Vapor Deposition). The etching stop layer 14 may include for example a 200 nm thick undoped $\text{Al}_x\text{Ga}_{1-x}\text{N}$ layer (e.g. $x=0.6$). The n-type semiconductor layer 20 includes an undoped high-purity layer 22, an n-type doped electron supply layer 24 having a bandgap greater than the high-purity layer 22, and an ohmic contact layer 26. The high-purity layer 22 may include for example a 10 nm thick undoped GaN layer. The electron supply layer 24 may include for example a 100 nm thick $\text{Al}_x\text{Ga}_{1-x}\text{N}$ layer (e.g. $x=0.25$) doped with Si at $1 \times 10^{18} \text{ cm}^{-3}$. The ohmic contact layer 26 may include for example a 30 nm thick GaN layer doped with Si at $4 \times 10^{18} \text{ cm}^{-3}$. The high-purity layer 22 and the electron supply layer 24 form a modulation doped structure, and a two-dimensional electron gas having high mobility is formed in the high-purity layer 22.

The electrical isolation layer 28 may include for example a 100 nm thick undoped GaN layer. The p-type semiconductor layer 30 includes an undoped high-purity layer 32 and a p-type

doped hole supply layer 34 having a bandgap greater than the high-purity layer 32. The high-purity layer 32 may include for example a 10 nm thick undoped GaN layer. The hole supply layer 34 may include for example a 100 nm thick $\text{Al}_x\text{Ga}_{1-x}\text{N}$ layer (e.g. $x=0.25$) doped with Mg at $1 \times 10^{19} \text{ cm}^{-3}$. The high-purity layer 32 and the hole supply layer 34 form a modulation doped structure, and a two-dimensional hole gas having high mobility is formed in the high-purity layer 32.

The isolation part 42 may be formed using for example the following method. Portions of the layers ranging from the p-type semiconductor layer 30 to the layer formed on the etching stop layer 14 are removed using etching to form a recess up to the upper surface of the etching stop layer 14. For example, a 500 nm thick insulator such as SiN or SiON is formed using CVD to fill the recess. Thereby, the isolation part 42 is formed. Also, the isolation part 42 may be formed by implanting ions to the semiconductor layer 38. Such ion implantation may be carried out for example using boron or oxygen under conditions of energy at 80 keV and a dose of $5 \times 10^{15} \text{ cm}^{-2}$. The absorption part 48 may include porous Au formed using vapor deposition. The cold pads 50 may include for example CrAu formed using vapor deposition. The passivation layer 40 may include for example a silicon oxide film or a silicon nitride film.

The p-type ohmic electrodes 46 and the p-type ohmic

electrodes 52 may include for example non-alloy ohmic electrodes made by forming a Ni layer on the p-type semiconductor layer 30 and an Al layer on the Ni layer using vapor deposition. The n-type ohmic electrodes 44 and the n-type ohmic electrodes 54 may include for example alloy ohmic electrodes made by forming a Ti layer on the n-type semiconductor layer 20, and an Al layer on the Ti layer using vapor deposition and then performing thermal treatment. The gate electrode 56 may include for example a Pt layer formed using vapor deposition.

FIGS. 2(a) ~ 2(d) are cross-sectional views showing a process of manufacturing the thermoelectric conversion element 100. As shown in FIG. 2(a), layers from the etching stop layer 14 to the p-type semiconductor layer 30 are formed on the substrate 10 using for example MOCVD. The isolation part 42 is formed. The p-type semiconductor layer 30 and the electrical isolation layer 28 corresponding to the region where the n-type thermoelectric conversion unit 90 is to be formed are removed. As such, the p-type semiconductor layer 30 and the electrical isolation layer 28 corresponding to the region where the transistor is to be formed are removed. The passivation layer 40 is formed so as to cover the p-type semiconductor layer 30 and the electrical isolation layer 28.

As shown in FIG. 2(b), portions of the passivation layer 40 are removed to form the p-type ohmic electrodes 46. As

such, the p-type ohmic electrodes 52 of the photoelectric conversion element 102 are formed. Portions of the passivation layer 40 are removed to form the n-type ohmic electrodes 44. As such, the n-type ohmic electrodes 54 of the transistor 104 are formed.

As shown in FIG. 2(c), the cold pads 50 are respectively formed so as to come into contact with the p-type ohmic electrode 46 and the n-type ohmic electrode 44. The absorption part 48 is formed so as to come into contact with the p-type ohmic electrode 46 and the n-type ohmic electrode 44. As shown in FIG. 2(d), the cavity 12 is formed on the substrate 10 using etching. In this case, etching of the n-type semiconductor layer 20 may be prevented by means of the etching stop layer 14.

The isolation part 42 and the passivation layer 40 are formed as shown in FIG. 2(a) and then the cavity 12 is formed as shown in FIG. 2(d) in this way, thereby preventing damage to the semiconductor layer 38 due to the formation of the cavity 12. In particular, the formation of the cavity 12 is performed after the procedures of FIGS. 2(a) ~ 2(c), whereby the procedures of FIGS. 2(a) ~ 2(c) may be carried out unhindered.

As shown in FIG. 2(b), it is preferred that any one type of the p-type ohmic electrodes 46 and the n-type ohmic electrodes 44 is formed using a non-alloy process (a non-

thermal treatment process) and the other type thereof is formed using an alloy process (a thermal treatment process for alloying). This is because the formation of the p-type ohmic electrodes 46 and the n-type ohmic electrodes 44 using an alloy process causes the alloy of one type of ohmic electrodes (thermal treatment for alloying) to break the alloy region of the other type of ohmic electrodes. Particularly in the case where the n-type semiconductor layer 20 and the p-type semiconductor layer 30 are stacked, it is preferred that ohmic electrodes that come into ohmic contact with the semiconductor layer located at an upper position among the n-type semiconductor layer 20 and the p-type semiconductor layer 30 are non-alloy ohmic electrodes, and that ohmic electrodes that come into ohmic contact with the semiconductor layer located at a lower position are alloy ohmic electrodes. If the ohmic electrodes on the semiconductor layer at the upper position are formed using an alloy process, the alloy region is distributed up to the semiconductor layer at the lower position. Thus, in the case where the semiconductor layer at the upper position is the p-type semiconductor layer 30 according to the first embodiment, the p-type ohmic electrodes 46 are preferably formed using a non-alloy process, and the n-type ohmic electrodes 44 are preferably formed using an alloy process. Also in the case where the n-type semiconductor layer is placed on the p-type semiconductor layer, the n-type

ohmic electrodes are preferably formed using a non-alloy process and the p-type ohmic electrodes are preferably formed using an alloy process. Thereby, the ohmic electrodes formed on the semiconductor layer at the upper position may be
5 prevented from being electrically connected to the semiconductor layer at the lower position.

With reference to FIG. 1, the thermoelectric conversion element 100 is described below. When the absorption part 48 absorbs for example IR rays, the temperature of the absorption
10 part 48 increases. Because of the temperature difference between the absorption part 48 and the cold pads 50, there may occur thermoelectric conversion due to Seebeck effect in the semiconductor layer of the p-type thermoelectric conversion unit 92 and the n-type thermoelectric conversion unit 90.
15 Thereby, an electromotive force is generated between the p-type ohmic electrodes 46 in the p-type thermoelectric conversion unit 92, and between the n-type ohmic electrodes 44 in the n-type thermoelectric conversion unit 90. The sensitivity R (V/W), detectability D (cm(Hz)^{1/2}/W) and response
20 time τ (sec) of the thermoelectric conversion element 100 are respectively represented by Equations 1, 2, 3 below.

Equation 1

$$R = \alpha \cdot N \cdot S \cdot R_{th}$$

Equation 2

$$D = R(A \cdot \Delta f / (4 \cdot k_B \cdot T \cdot R_{el}))^{1/2}$$

Equation 3

$$\tau = R_{th} \cdot C$$

wherein α is the thermal absorption coefficient, N is a
 5 logarithm when a pair of the p-type thermoelectric conversion
 unit 92 and the n-type thermoelectric conversion unit 90 are
 connected in a series (which will be described in detail
 later), S is the Seebeck coefficient, R_{th} is the thermal
 resistance of the semiconductor layer, A is the area of the
 10 absorption part 48, Δf is the bandwidth, k_B is the Boltzmann
 coefficient, T is the absolute temperature, R_{el} is the
 electrical resistance of the semiconductor layer, and C is the
 heat capacity of the thermoelectric conversion unit.

In Equation 1, thermal resistance R_{th} of the semiconductor
 15 layer should be increased to increase the sensitivity R.
 Hence, the semiconductor layer of the p-type thermoelectric
 conversion unit 92 and the n-type thermoelectric conversion
 unit 90 is thinned and provided in the form of a beam, and the
 cavity 12 is formed on the substrate 10, thereby increasing
 20 the thermal resistance R_{th} of the semiconductor layer.
 However, when the p-type thermoelectric conversion unit 92 and
 the n-type thermoelectric conversion unit 90 are thinned and
 provided in the form of beam, the electrical resistance R_{el} of
 the semiconductor layer may increase. Thereby, the

detectability D decreases. Accordingly, the n-type semiconductor layer 20 and the p-type semiconductor layer 30 include a modulation doped structure, so that two-dimensional electrons and two-dimensional holes, having high mobility, are
5 formed. Thus, the electrical resistance R_{e1} of the n-type semiconductor layer 20 and the p-type semiconductor layer 30 may decrease. Thereby, both desired sensitivity R and detectability D may be obtained.

Also with reference to FIG. 1, the photoelectric
10 conversion element 102 is described below. The photoelectric conversion element 102 has a PIN structure comprising the p-type semiconductor layer 30, the electrical isolation layer 28 and the n-type semiconductor layer 20. The PIN structure enables the photoelectric conversion of irradiated light.

15 Also with reference to FIG. 1, the transistor 104 is described below. The transistor 104 has a HEMT (High Electron Mobility Transistor) structure having a two-dimensional electron gas channel formed in the modulation doped structure of the n-type semiconductor layer 20. In this way, the n-type
20 semiconductor layer 20 which is a portion of the semiconductor layer 38 may be used as an operating layer. In the transistor 104, the p-type semiconductor layer 30 may be used as an operating layer. Also in the transistor 104, the gate electrode 56 is able to act as an anode and the n-type ohmic
25 electrodes 54 are able to act as a cathode, so that the

transistor 104 may function as a diode.

According to the first embodiment, the thermoelectric conversion element 100 includes the semiconductor layer 38 that performs thermoelectric conversion. In the photoelectric conversion element 102, at least a portion of the semiconductor layer 38 performs photoelectric conversion. Thus, when the photoelectric conversion element 102 performs photoelectric conversion using at least the portion of the semiconductor layer 38 that performs thermoelectric conversion in this way, the thermoelectric conversion element 100 and the photoelectric conversion element 102 may be monolithically integrated. The thermoelectric conversion element 100 enables the detection of light in a wide range from far IR to near IR. Meanwhile, the photoelectric conversion element 102 detects light in a narrow range corresponding to the bandgap of the semiconductor layer. Thus, monolithic integration of a wide-range detector and a narrow-range detector is possible.

Also in the transistor 104, at least a portion of the semiconductor layer 38 may be used as an operating layer. Thereby, the thermoelectric conversion element 100 and the transistor 104 may be monolithically integrated. Alternatively instead of the transistor, for example a diode may be utilized.

As mentioned above, the thermoelectric conversion element 100, and at least one of the photoelectric conversion element

102 and the transistor 104 may be monolithically integrated. Alternatively instead of the transistor, for example a diode may be used.

Furthermore, the semiconductor layer 38 includes a layer
5 having bandgap energy corresponding to UV light (in the first embodiment, a GaN layer, an AlGaN layer), and at least a portion of the semiconductor layer 38 of the photoelectric conversion element 102 performs the photoelectric conversion of UV light. Hence, the photoelectric conversion element 102
10 may act as a UV detector for detecting UV light. The absorption part 48 of the thermoelectric conversion element 100 may act as an IR absorption part that absorbs IR rays and converts them into heat. Hence, the thermoelectric conversion element 100 may act as an IR detector for detecting IR rays.
15 Thereby, the UV detector and the IR detector may be monolithically integrated.

FIG. 3 shows the bandgap energy with respect to the lattice constant of a variety of semiconductors. The semiconductor layer having a bandgap corresponding to UV light
20 may include a semiconductor layer 38 made of GaN or a mixture of crystals of AlN and GaN as illustrated in the first embodiment. Alternatively a semiconductor layer containing ZnO may be used. For example, ZnO or a mixture of crystals of ZnO and MgO may be used for the semiconductor layer. Also,
25 ZnS, ZnSe, MgS or MgSe may be used.

The semiconductor layer 38 includes the p-type semiconductor layer 30 and the n-type semiconductor layer 20 which are stacked. The thermoelectric conversion element 100 includes the p-type thermoelectric conversion unit 92 wherein
5 the p-type semiconductor layer 30 performs thermoelectric conversion, and the n-type thermoelectric conversion unit 90 wherein the n-type semiconductor layer 20 performs thermoelectric conversion. Thereby, thermoelectric conversion may be carried out at high sensitivity.

10 Also, the photoelectric conversion element 102 is a photodiode that uses the p-type semiconductor layer 30 and the n-type semiconductor layer 20. Thereby, monolithic integration of the thermoelectric conversion element 100 and the photoelectric conversion element 102 becomes much more
15 feasible.

Also, the isolation part 42 is provided between the p-type thermoelectric conversion unit 92 and the n-type thermoelectric conversion unit 90 so as to electrically isolate the p-type semiconductor layer 30 and the n-type
20 semiconductor layer 20. Thereby, interference between the p-type semiconductor layer 30 and the n-type semiconductor layer 20 may be prevented.

FIG. 4 is a cross-sectional view showing a modification of the first embodiment. As shown in FIG. 4, a cavity 12a may
25 also be formed on the substrate 10 under the photoelectric

conversion element 102. When the cavity 12a is formed on the substrate 10 under the photoelectric conversion element 102 in this way, noise caused by the absorption of light due to photoelectric effects may be suppressed in the substrate 10
5 made of for example Si.

(Second Embodiment)

According to a second embodiment, there is provided a thermoelectric conversion apparatus. FIG. 5 is a cross-
10 sectional view showing the thermoelectric conversion apparatus according to the second embodiment. As shown in FIG. 5, the thermoelectric conversion apparatus is configured such that a first thermoelectric conversion element 100a and a second thermoelectric conversion element 100b as described in the
15 first embodiment are connected in a series. Also, a first n-type thermoelectric conversion unit 90a and a first p-type thermoelectric conversion unit 92a of the first thermoelectric conversion element 100a, and a second n-type thermoelectric conversion unit 90b and a second p-type thermoelectric
20 conversion unit 92b of the second thermoelectric conversion element 100b are connected in a series.

FIG. 6 is a top plan view showing the thermoelectric conversion apparatus according to the second embodiment. The thermoelectric conversion apparatus includes a central region
25 72, a first beam 70a and a second beam 70b. The first beam

70a and the second beam 70b are separated from the substrate 10 by means of cavities 12 as shown in FIG. 5. One end of each of the first beam 70a and the second beam 70b is mechanically connected to the central region 72. The other
5 end of each of the first beam 70a and the second beam 70b is mechanically connected to an external support 74. The first beam 70a is provided with the first n-type thermoelectric conversion unit 90a of the first thermoelectric conversion element 100a and the second p-type thermoelectric conversion
10 unit 92b of the second thermoelectric conversion element 100b. The semiconductor layer between the first n-type thermoelectric conversion unit 90a and the second p-type thermoelectric conversion unit 92b is electrically isolated by means of a second isolation part 42a. The second beam 70b is
15 provided with the second n-type thermoelectric conversion unit 90b of the second thermoelectric conversion element 100b and the first p-type thermoelectric conversion unit 92a of the first thermoelectric conversion element 100a. The semiconductor layer between the second n-type thermoelectric
20 conversion unit 90b and the first p-type thermoelectric conversion unit 92a is electrically isolated by means of a third isolation part 42b.

Provided at the center of the central region 72 is an absorption part 48. Also provided around the central region
25 72 is a first wire 45a that connects n-type ohmic electrodes

44 of the first n-type thermoelectric conversion unit 90a and p-type ohmic electrodes 46 of the first p-type thermoelectric conversion unit 92a. Furthermore, a second wire 45b is provided, which connects n-type ohmic electrodes 44 of the second n-type thermoelectric conversion unit 90b and p-type ohmic electrodes 46 of the second p-type thermoelectric conversion unit 92b. Moreover, a first isolation part 42c of the central region 72 is provided between the absorption part 48 and the first wire 45a and between the absorption part 48 and the second wire 45b, and functions to electrically isolate the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b. Also, the p-type ohmic electrode 46 positioned between the lower surface of the absorption part 48 and the upper surface of the first isolation part 42c is thermally connected to the absorption part 48. The first isolation part 42c underneath the p-type ohmic electrode 46 is represented by a dashed line. Also, the p-type ohmic electrode 46 underneath the absorption part 48 is represented by a dashed line. The other end of each of the first beam 70a and the second beam 70b is provided with the cold pad 50. The second isolation part 42a, the third isolation part 42b and the first isolation part 42c function to electrically isolate the semiconductor layer 38 on the etching stop layer 14 as in the isolation part 42 according to the first embodiment. The width and length of each of the

first beam 70a and the second beam 70b may be for example 6 μm and 152 μm , respectively. Each side of the central region 72 is for example 52 μm .

According to the second embodiment, the first beam 70a
5 and the second beam 70b are provided with the thermoelectric conversion units, thereby greatly increasing thermal resistance and sensitivity. The first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b are connected in a series so that the
10 first p-type thermoelectric conversion unit 92a and the second n-type thermoelectric conversion unit 90b are connected to the support 74 at the left lower position of FIG. 6. The first n-type thermoelectric conversion unit 90a and the second p-type thermoelectric conversion unit 92b are provided to the first
15 beam 70a. The second n-type thermoelectric conversion unit 90b and the first p-type thermoelectric conversion unit 92a are provided to the second beam 70b. Thereby, the logarithm N of Equation 1 may be set to 2, thus greatly increasing the sensitivity.

20 In the central region 72 to which the first beam 70a and the second beam 70b are connected, the first isolation part 42c is further provided, which electrically isolates at least one of the p-type semiconductor layer 30 and the n-type semiconductor layer 20 between the first thermoelectric
25 conversion element 100a and the second thermoelectric

conversion element 100b. In the case where the central region 72 includes at least one of the p-type semiconductor layer 30 and the n-type semiconductor layer 20, the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b may electrically interfere due to the semiconductor layer at the central region 72. Hence, the first isolation part 42c electrically isolates at least one of the p-type semiconductor layer 30 and the n-type semiconductor layer 20. Thereby, electrical interference between the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b may be prevented. Particularly in the case where at least one of the p-type ohmic electrodes 46 and the n-type ohmic electrodes 44 is formed using an alloy process, electrical interference between the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b may be facilitated due to the conductive semiconductor layer corresponding to the ohmic electrode formed using an alloy process. Accordingly, it is preferred that the first isolation part 42c of the central region 72 electrically isolates the conductive semiconductor layer corresponding to the ohmic electrode formed using an alloy process.

Also, the first beam 70a preferably includes the second isolation part 42a that electrically isolates the first n-type thermoelectric conversion unit 90a and the second p-type

thermoelectric conversion unit 92b, and the second beam 70b preferably includes the third isolation part 42b that electrically isolates the first p-type thermoelectric conversion unit 92a and the second n-type thermoelectric conversion unit 90b. Thereby, electrical interference between the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b in the first beam 70a and the second beam 70b may be further prevented.

FIGS. 7(a) and 7(b) are top plan views showing modifications of the second embodiment. As shown in FIG. 7(a), the photoelectric conversion element 102 may be provided in the central region 72. As shown in FIG. 7(b), both the photoelectric conversion element 102 and the absorption part 48 may be provided in the central region 72.

FIGS. 8(a) ~ 8(c) are top plan views showing the other modifications of the second embodiment. As shown in FIG. 8(a), the first isolation part 42c of the central region 72 may be provided so as to cross the absorption part 48. The first isolation part 42c under the absorption part 48 is represented by a dotted line. As shown in FIG. 8(b), the first isolation part 42c is provided between the absorption part 48 and the wire 45b, and may not be provided between the absorption part 48 and the wire 45a. As shown in FIG. 8(c), the first isolation part 42c is provided between the absorption part 48 and the wire 45a, and may not be formed

between the absorption part 48 and the wire 45b. In this way, the first isolation part 42c may be provided so as to electrically isolate the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b. In particular, the first isolation part 42c is provided so that there is no spacing between the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b, whereby the first thermoelectric conversion element 100a and the second thermoelectric conversion element 100b may be completely electrically isolated.

The sensitivity R and the detectability D of the thermoelectric conversion apparatus using GaN and AlGaN are calculated. First, the sensitivity R is calculated using Equation 1. It is supposed that the thermal absorption coefficient α is 1, the logarithm N is 2 and the Seebeck coefficient S of GaN is $1500 \mu\text{V/K}$. The thermal resistance R_{th} is calculated from the length L of each of the first beam 70a and the second beam 70b, the width W of each of the p-type thermoelectric conversion unit 92 and the n-type thermoelectric conversion unit 90, and the thicknesses t_p , t_n of the semiconductor layer of the p-type thermoelectric conversion unit 92 and the n-type thermoelectric conversion unit 90. For example, at $L = 137 \mu\text{m}$, $W = 1.5 \mu\text{m}$, $t_p = 0.55 \mu\text{m}$ and $t_n = 0.34 \mu\text{m}$, R_{th} is $3.4 \times 10^5 \text{ K/W}$. As such, the sensitivity

R is 2000 V/W.

FIG. 9(a) shows the sensitivity R with respect to changes in L and W of the thermoelectric conversion apparatus using AlGaIn/GaN. As shown in FIG. 9(a), the sensitivity R increases in proportion to an increase in L and to a decrease in W.

The detectability D is calculated using Equation 2. On the assumption of bandwidth $\Delta f = 1$ and the absolute temperature $T = 300\text{K}$, the area A of the absorption part is supposed to be in proportion to L as shown in FIG. 9(a). The electrical resistance R_{e1} is calculated from L and W. For example, at the area $A = 52 \times 52 \mu\text{m}^2$, $L = 137 \mu\text{m}$ and $W = 1.5 \mu\text{m}$, R_{e1} is 320 k Ω . As such, the detectability D is $7 \times 10^8 \text{ cm}(\text{Hz})^{1/2}/\text{W}$. On the assumption that the heat capacity C is $4 \times 10^{-9} \text{ J/K}$, the response time τ is 1.3 ms.

FIG. 9(b) shows the detectability D and the response time τ with respect to changes in L and W. As shown in FIG. 9(b), the detectability D increases in proportion to an increase in L and to a decrease in W.

As in FIGS. 9(a) and 9(b), the sensitivity R and the detectability D of the thermoelectric conversion apparatus using ZnO and ZnMgO are calculated. First, the sensitivity R is calculated using Equation 1. It is supposed that the thermal absorption coefficient α is 1, the logarithm N is 2, and the Seebeck coefficient S of ZnO is 1140 $\mu\text{V/K}$. As in FIG. 9(a), the thermal resistance R_{th} is calculated from L, W, t_p

and t_n . For example, at $L = 137 \text{ } \mu\text{m}$, $W = 1.5 \text{ } \mu\text{m}$, $t_p = 0.55 \text{ } \mu\text{m}$ and $t_n = 0.34 \text{ } \mu\text{m}$, R_{th} is $1.75 \times 10^6 \text{ K/W}$. As such, the sensitivity R is 8000 V/W .

FIG. 10(a) shows the sensitivity R with respect to changes in L and W . As shown in FIG. 10(a), R increases in proportion to an increase in L and to a decrease in W .

The detectability D is calculated using Equation 2. On the assumption of bandwidth $\Delta f = 1$ and the absolute temperature $T = 300\text{K}$, the area A of the absorption part is supposed to be in proportion to L as shown in FIG. 10(a). The electrical resistance R_{el} is calculated from L and W . For example, at the area $A = 52 \times 52 \text{ } \mu\text{m}^2$, $L = 137 \text{ } \mu\text{m}$ and $W = 1.5 \text{ } \mu\text{m}$, R_{el} is $310 \text{ k}\Omega$. As such, the detectability D is $8 \times 10^8 \text{ cm(Hz)}^{1/2}/\text{W}$. On the assumption that the heat capacity C is $5.3 \times 10^{-9} \text{ J/K}$, the response time τ is 9.2 ms .

FIG. 10(b) shows the detectability D and the response time τ with respect to changes in L and W . As shown in FIG. 10(b), the detectability D increases in proportion to an increase in L and to a decrease in W .

As shown in FIGS. 9(a) ~ 10(b), it is preferred that the beam length L is $100 \text{ } \mu\text{m}$ or more. Particularly in the AlGaIn/GaN modulation doped structure or in the ZnO/MgZnO modulation doped structure, the beam length L may be $100 \text{ } \mu\text{m}$ or more.

The thermoelectric conversion apparatus according to the

second embodiment, and at least one of the photoelectric conversion element and the transistor according to the first embodiment may be monolithically integrated.

5 **Mode for Invention**

(Third Embodiment)

According to a third embodiment, there is provided a photoelectric conversion element that detects IR rays. As shown in FIG. 1 according to the first embodiment, the etching
10 stop layer 14 may include for example a 200 nm thick undoped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer (e.g. $x=0.6$). The high-purity layer 22 may include for example a 10 nm thick undoped $\text{In}_x\text{Ga}_{1-x}\text{As}$ layer (e.g. $x=0.25$). The electron supply layer 24 may include for example a 100 nm thick $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer (e.g. $x=0.25$) doped with Si at
15 $1 \times 10^{18} \text{ cm}^{-3}$. The ohmic contact layer 26 may include for example a 30 nm thick GaAs layer doped with Si at $4 \times 10^{18} \text{ cm}^{-3}$.

The electrical isolation layer 28 may include for example a 100 nm thick undoped GaAs layer. The high-purity layer 32 may include for example a 10 nm thick undoped $\text{In}_x\text{Ga}_{1-x}\text{As}$ layer
20 (e.g. $x=0.25$). The hole supply layer 34 may include for example a 100 nm thick $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer (e.g. $x=0.25$) doped with Zn at $1 \times 10^{19} \text{ cm}^{-3}$.

The p-type ohmic electrodes 46 and the p-type ohmic electrodes 52 may include for example non-alloy ohmic
25 electrodes made by forming a Ti layer on the p-type

semiconductor layer 30, and an Au layer on the Ti layer using vapor deposition. The n-type ohmic electrodes 44 and the n-type ohmic electrodes 54 may include for example alloy ohmic electrodes made by forming an AuGe layer on the n-type semiconductor layer, and a Ni layer on the AuGe layer using
5 vapor deposition and then performing thermal treatment.

The sensitivity R and the detectability D of the same thermoelectric conversion apparatus as in the second embodiment are calculated. First, the sensitivity R is
10 calculated using Equation 1. It is supposed that the thermal absorption coefficient α is 1, the logarithm N is 2 and the Seebeck coefficient S of GaN is $1250 \mu\text{V/K}$. For example, at $L = 137 \mu\text{m}$, $W = 1.5 \mu\text{m}$, $t_p = 0.55 \mu\text{m}$ and $t_n = 0.34 \mu\text{m}$, R_{th} is $3.6 \times 10^6 \text{ K/W}$. As such, the sensitivity R is 1800 V/W .

15 FIG. 11(a) shows the sensitivity R with respect to changes in L and W . As shown in FIG. 11(a), R increases in proportion to an increase in L and to a decrease in W .

The detectability D is calculated using Equation 2. On the assumption of bandwidth $\Delta f = 1$ and the absolute
20 temperature $T = 300\text{K}$, the area A of the absorption part 48 is supposed to be in proportion to L as shown in FIG. 11(a). The electrical resistance R_{e1} is calculated from L and W . For example, at the area $A = 52 \times 52 \mu\text{m}^2$, $L = 137 \mu\text{m}$ and $W = 1.5 \mu\text{m}$, R_{e1} is $420 \text{ k}\Omega$. As such, the detectability D is 2.27×10^9
25 $\text{cm}(\text{Hz})^{1/2}/\text{W}$. On the assumption that the heat capacity C is

3.5×10^{-9} J/K, the response time τ is 13 ms.

FIG. 11(b) shows the detectability D and the response time τ with respect to changes in L and W . As shown in FIG. 11(b), the detectability D increases in proportion to an
5 increase in L and to a decrease in W .

As shown in FIGS. 9(a) ~ 11(b), in the case where the thermoelectric conversion element is formed using the semiconductor layer including GaN as in the second embodiment, the sensitivity R and the detectability D are lower than in
10 the thermoelectric conversion element including GaAs according to the third embodiment, but the response time τ may be faster. According to the third embodiment, the sensitivity R and the detectability D of the thermoelectric conversion element including GaAs may increase.

15 According to the third embodiment, the semiconductor layer 38 includes a layer (e.g. InGaAs) having bandgap energy corresponding to IR rays. In the photoelectric conversion element 102, at least a portion of the semiconductor layer converts IR rays into an electrical signal. Thereby, the
20 thermoelectric conversion element 100 may detect IR rays in the wide range from far IR to near IR. On the other hand, the photoelectric conversion element 102 may detect IR rays corresponding to the bandgap of the semiconductor layer. Thus, the wide-range IR detector (which is a far IR detector
25 at a wavelength of about 10 μm) and the narrow-range IR

detector (which is a near IR detector at a wavelength of about 1 μm) may be monolithically integrated. The third embodiment may be applied to for example an image sensor for detecting both the wide-range IR rays and the narrow-range IR rays.

5

(Forth Embodiment)

According to a fourth embodiment, there is provided an image sensor comprising thermoelectric conversion elements 100 and photoelectric conversion elements 102 which are
10 integrated. FIG. 12 is a block diagram showing the fourth embodiment. Here, the thermoelectric conversion elements 100 and the photoelectric conversion elements 102 are arranged in the shape of a matrix. As these thermoelectric conversion elements 100 and photoelectric conversion elements 102, the
15 thermoelectric conversion element 100 and the photoelectric conversion element 102 illustrated according to the first to third embodiments may be used. Each of the thermoelectric conversion elements 100 and the photoelectric conversion elements 102 is disposed between the source and the gate of a
20 selective transistor 64. The gate of the selective transistor 64 is connected to a row selection line 68, and the drain is connected to a column selection line 66. A row selection part 62 and a column selection part 60 select the row selection line 68 and the column selection line 66, thus outputting a
25 signal from predetermined thermoelectric conversion element

100 and photoelectric conversion element 102.

According to the fourth embodiment, as shown in FIG. 12, a plurality of thermoelectric conversion elements 100 and a plurality of photoelectric conversion elements 102 are
5 arranged in the shape of a matrix. The selection part (e.g. the selective transistor 64, the row selection part 62 and the column selection part 60) selects at least one among the pluralities of thermoelectric conversion elements 100 and photoelectric conversion elements 102. Thereby, the signal of
10 the selected one among the pluralities of thermoelectric conversion elements 100 and photoelectric conversion elements 102 may be output.

In the fourth embodiment, a transistor 104 is used as the selective transistor 64, the row selection part 62 and the
15 column selection part 60. Briefly, the selection part includes the transistor 104. Thereby, the thermoelectric conversion elements 100 and the photoelectric conversion elements 102 of the image sensor may be monolithically integrated. Exemplary is an image sensor comprising
20 integrated IR detector and UV detector. Also exemplary is an image sensor comprising integrated far IR detector and near IR detector.

According to the first to third embodiments, the semiconductor layer 38 may include for example AlGaIn, GaN, ZnO, MgZnO, AlGaAs, InGaAs, and additionally for example, InP,
25

InAlAs, GaAs, InGaP, InAs, InGaN, SiC, ZnCdO, CdO, MgO, CdO, ZnMgS, ZnS, ZnSe, MgS, MgSe, Si, SiGe and combinations thereof.

The modulation doped structure in the n-type semiconductor layer 20 and the p-type semiconductor layer 30 may include for example, AlGaN/GaN, MgZnO/ZnO and AlGaAs/InGaAs, and additionally for example, InP/InGaAs, InAlAs/InP, InAlAs/InGaAs, AlGaAs/AlGaAs, AlGaAs/GaAs, AlGaAs/InAs, InGaP/InGaAs, InGaP/AlGaAs, InGaP/GaAs, InGaN/InAs, AlGaN/AlGaN, AlGaN/InGaN, AlInN/InGaN, AlGaN/SiC, GaN/SiC, GaN/InGaN, ZnMgO/ZnCdO, ZnCdO/CdO, MgO/ZnCdO, MgO/ZnO, ZnO/CdO, CdMgO/CdO, ZnMgS/ZnS, ZnS/ZnSe, MgS/MgSe, MgSe/ZnSe, MgS/ZnS, and Si/SiGe.

The substrate 10 may include, depending on the type of the semiconductor layer 38, a Si substrate, and additionally for example a Si substrate having a B-doped Si epitaxial layer formed thereon, a Si substrate having B ions implanted thereto, a Si substrate having an insulating layer of silicon oxide or silicon nitride formed thereon, a GaAs substrate, an InP substrate, a GaN substrate, a SiC substrate, a ZnO substrate, a sapphire substrate, a sapphire substrate having an insulating layer of silicon oxide, silicon nitride or aluminum nitride formed thereon, or a glass substrate.

Although the first to third embodiments describe the absorption of IR rays by means of the absorption part 48, the

absorption part 48 may absorb other electromagnetic waves, such as micro waves, etc. The absorption part absorbing the micro waves may be provided with for example an antenna that receives micro waves and a resistor or a diode for converting
5 power of the micro waves received by the antenna into heat.

Although the preferred embodiments of the present invention have been disclosed for illustrative purposes, the present invention is not limited to such specific embodiments, and various modifications and variations are possible, without
10 departing from the scope and spirit of the invention as disclosed in the accompanying claims.

CLAIMS

1. An electronic apparatus, comprising:

a thermoelectric conversion element including a
5 semiconductor layer which performs thermoelectric conversion
using Seebeck effect, and

at least one of a photoelectric conversion element in
which at least a portion of the semiconductor layer performs
photoelectric conversion and a transistor or a diode having at
10 least a portion of the semiconductor layer as an operating
layer,

wherein the semiconductor layer has bandgap energy
corresponding to UV light,

the thermoelectric conversion element has an IR
15 absorption part which absorbs IR rays and converts them into
heat, and

at least the portion of the semiconductor layer of the
photoelectric conversion element performs photoelectric
conversion of UV light.

20

2. An electronic apparatus, comprising:

a thermoelectric conversion element including a
semiconductor layer which performs thermoelectric conversion
using Seebeck effect, and

25 at least one of a photoelectric conversion element in

which at least a portion of the semiconductor layer performs photoelectric conversion and a transistor or a diode having at least a portion of the semiconductor layer as an operating layer,

5 wherein the semiconductor layer has bandgap energy corresponding to IR rays,

 the thermoelectric conversion element has an IR absorption part which absorbs IR rays and converts them into heat, and

10 at least the portion of the semiconductor layer of the photoelectric conversion element performs photoelectric conversion of IR rays.

3. The electronic apparatus of claim 1 or 2, wherein the
15 semiconductor layer includes a p-type semiconductor layer and an n-type semiconductor layer which are stacked, and

 the thermoelectric conversion element includes a p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion and an
20 n-type thermoelectric conversion unit wherein the n-type semiconductor layer performs thermoelectric conversion.

4. An electronic apparatus, comprising:

 a thermoelectric conversion element including a
25 semiconductor layer which performs thermoelectric conversion

using Seebeck effect, and

at least one of a photoelectric conversion element in which at least a portion of the semiconductor layer performs photoelectric conversion and a transistor or a diode having at least a portion of the semiconductor layer as an operating layer,

wherein the semiconductor layer includes a p-type semiconductor layer and an n-type semiconductor layer which are stacked,

the thermoelectric conversion element includes a p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion and an n-type thermoelectric conversion unit wherein the n-type semiconductor layer performs thermoelectric conversion, and

the photoelectric conversion element is a photodiode that uses the p-type semiconductor layer and the n-type semiconductor layer.

5. An electronic apparatus, comprising:

a thermoelectric conversion element including a semiconductor layer which performs thermoelectric conversion using Seebeck effect, and

at least one of a photoelectric conversion element in which at least a portion of the semiconductor layer performs photoelectric conversion and a transistor or a diode having at

least a portion of the semiconductor layer as an operating layer,

wherein the semiconductor layer includes a p-type semiconductor layer and an n-type semiconductor layer which
5 are stacked,

the thermoelectric conversion element includes a p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion and an n-type thermoelectric conversion unit wherein the n-type
10 semiconductor layer performs thermoelectric conversion, and

an isolation part is provided between the p-type thermoelectric conversion unit and the n-type thermoelectric conversion unit so as to electrically isolate the p-type semiconductor layer and the n-type semiconductor layer.

15

6. An electronic apparatus, comprising:

a thermoelectric conversion element including a semiconductor layer which performs thermoelectric conversion using Seebeck effect, and

20 at least one of a photoelectric conversion element in which at least a portion of the semiconductor layer performs photoelectric conversion and a transistor or a diode having at least a portion of the semiconductor layer as an operating layer,

25 wherein the semiconductor layer includes a p-type

semiconductor layer and an n-type semiconductor layer which are stacked,

the thermoelectric conversion element includes a p-type thermoelectric conversion unit wherein the p-type semiconductor layer performs thermoelectric conversion and an
5 n-type thermoelectric conversion unit wherein the n-type semiconductor layer performs thermoelectric conversion, and

an ohmic electrode formed on the semiconductor layer disposed at an upper position among the p-type semiconductor
10 layer and the n-type semiconductor layer is a non-alloy ohmic electrode, and an ohmic electrode formed on the semiconductor layer disposed at a lower position among the p-type semiconductor layer and the n-type semiconductor layer is an alloy ohmic electrode.

15

7. An electronic apparatus, comprising:

a thermoelectric conversion element including a semiconductor layer which performs thermoelectric conversion using Seebeck effect, and

20 at least one of a photoelectric conversion element in which at least a portion of the semiconductor layer performs photoelectric conversion and a transistor or a diode having at least a portion of the semiconductor layer as an operating layer,

25 wherein the semiconductor layer has a modulation doped

structure.

8. The electronic apparatus of any one of claims 1 to 7,
wherein the thermoelectric conversion element and the
5 photoelectric conversion element are provided in plural
numbers such that the plurality of thermoelectric conversion
elements and the plurality of photoelectric conversion
elements are arranged in a matrix shape, and a selection part
is provided so as to select at least one among the plurality
10 of thermoelectric conversion elements and the plurality of
photoelectric conversion elements and includes the transistor.

9. The electronic apparatus of claim 1 or 2, wherein the
semiconductor layer includes a p-type semiconductor layer and
15 an n-type semiconductor layer which are stacked, and

the thermoelectric conversion element comprises:

a first thermoelectric conversion element including a
first n-type thermoelectric conversion unit wherein the n-type
semiconductor layer performs thermoelectric conversion and a
20 first p-type thermoelectric conversion unit wherein the p-type
semiconductor layer performs thermoelectric conversion,

a second thermoelectric conversion element including a
second n-type thermoelectric conversion unit wherein the n-
type semiconductor layer performs thermoelectric conversion
25 and a second p-type thermoelectric conversion unit wherein the

p-type semiconductor layer performs thermoelectric conversion,

a first beam including the first n-type thermoelectric conversion unit and the second p-type thermoelectric conversion unit,

5 a second beam including the first p-type thermoelectric conversion unit and the second n-type thermoelectric conversion unit, and

a central region to which the first beam and the second beam are connected and which includes a first isolation part
10 for electrically isolating at least one of the p-type semiconductor layer and the n-type semiconductor layer between the first thermoelectric conversion element and the second thermoelectric conversion element,

wherein the first thermoelectric conversion element and
15 the second thermoelectric conversion element are connected in a series so that the first n-type thermoelectric conversion unit and the second p-type thermoelectric conversion unit are connected.

20 10. The electronic apparatus of claim 9, wherein the first beam includes a second isolation part for electrically isolating the first n-type thermoelectric conversion unit and the second p-type thermoelectric conversion unit, and the second beam includes a third isolation part for electrically
25 isolating the first p-type thermoelectric conversion unit and

the second n-type thermoelectric conversion unit.